WNSC2D201200W



Rev.02 - 15 July 2024

Product data sheet

1. General description

WeEn Se

Dual Silicon Carbide Schottky diodes in a TO247-2L plastic package, designed for high frequency switching mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T_{j(max)} = 175 °C)

3. Applications

- Switching mode power supplies
- UPS & energy storage systems
- PV inverter and MPPT circuit
- Battery formation systems
- EV chargers
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	/ _{RRM} repetitive peak reverse 1200				V		
I _F	continuous forward current	T _{mb} ≤ 144 °C, DC; <u>Fig. 2</u>		20		А	
Tj	junction temperature			175		°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.65	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.95	2.30	V
		I _F = 20 A; T _j = 175 °C; <u>Fig. 5</u>		-	2.10	2.60	V
Dynamic	characteristics	1					
Q _r	recovered charge	$I_F = 20 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$		-	45	-	nC

5. Pinning information

Table 2. P	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathode	ГЛ ГЛ Г ГЛ Г Г К А ТО247-2L	

6. Ordering information

Table 3. Ordering information							
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
WNSC2D201200W	TO247-2L	WNSC2D201200W6Q	Tube	30	TO247L-2L(L) TO247L-2L(P)		

7. Marking

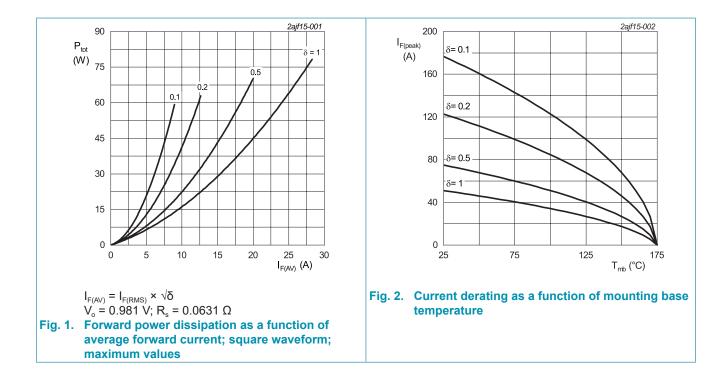
Table 4. Marking codes					
Type number	Marking codes				
WNSC2D201200W	WNSC2D				
	201200W				

8. Limiting values

Table 5. Limiting values

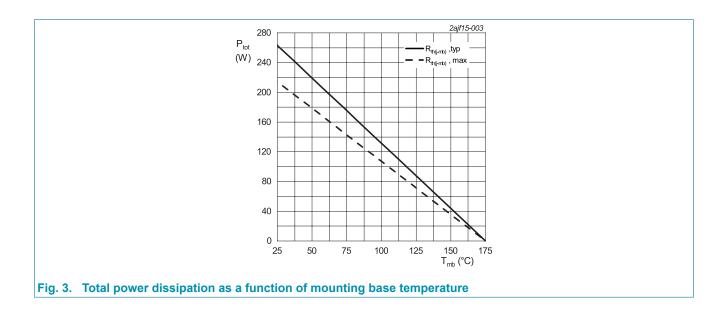
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V _R	reverse voltage	DC	1200	V
I _F	continuous forward	T _{mb} ≤ 144 °C; DC; <u>Fig. 2</u>	20	А
	current	T _{mb} ≤ 125°C; DC; <u>Fig. 2</u>	27	А
		$T_{mb} \leq 25^{\circ}C; DC; Fig. 2$	51	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 125 °C; square-wave pulse	40	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	160	А
		t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	1000	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	128	A ² s
T _{stg}	storage temperature		-55 to 175	°C
Tj	junction temperature		175	°C



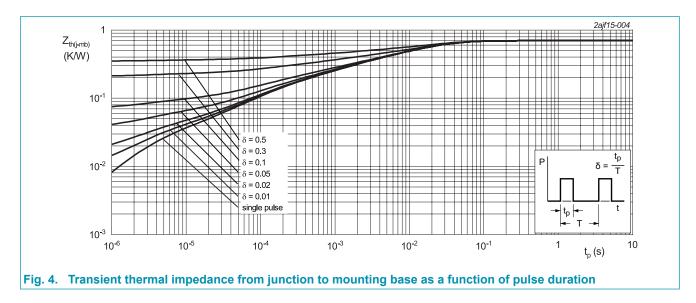
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WNSC2D201200W Silicon Carbide Diode



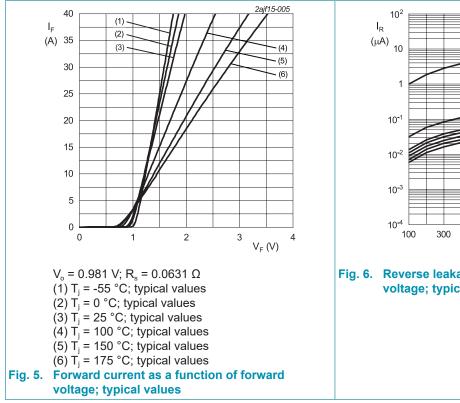
9. Thermal characteristics

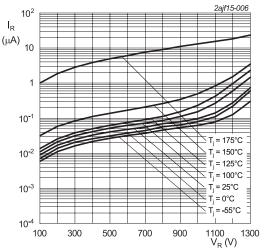
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.57	0.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W



10. Characteristics

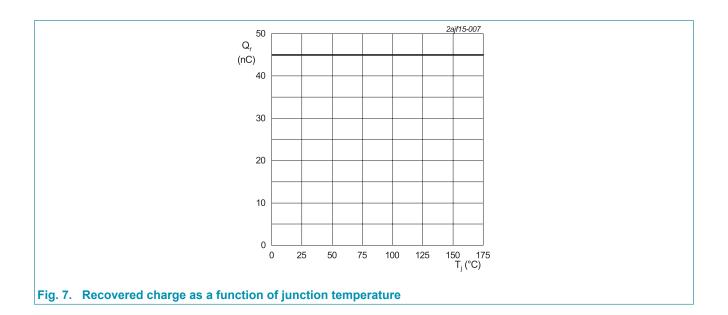
Table 7. Cl	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.45	1.65	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.95	2.30	V
		I _F = 20 A; T _j = 175 °C; <u>Fig. 5</u>	-	2.10	2.60	V
I _R	reverse current	V _R = 1200 V; T _j = 25 °C; <u>Fig. 6</u>	-	1	100	μA
		V _R = 1200 V; T _j = 175 °C; <u>Fig. 6</u>	-	25	1000	μA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 20 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	45	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	950	-	pF
		f = 1 MHz; V _R = 400 V; T _j = 25 °C	-	86	-	pF
		f = 1 MHz; V _R = 800 V; T _j = 25 °C	-	64	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 5.3 A; L = 10 mH; T _{j(init)} = 25 °C	140	-	-	mJ



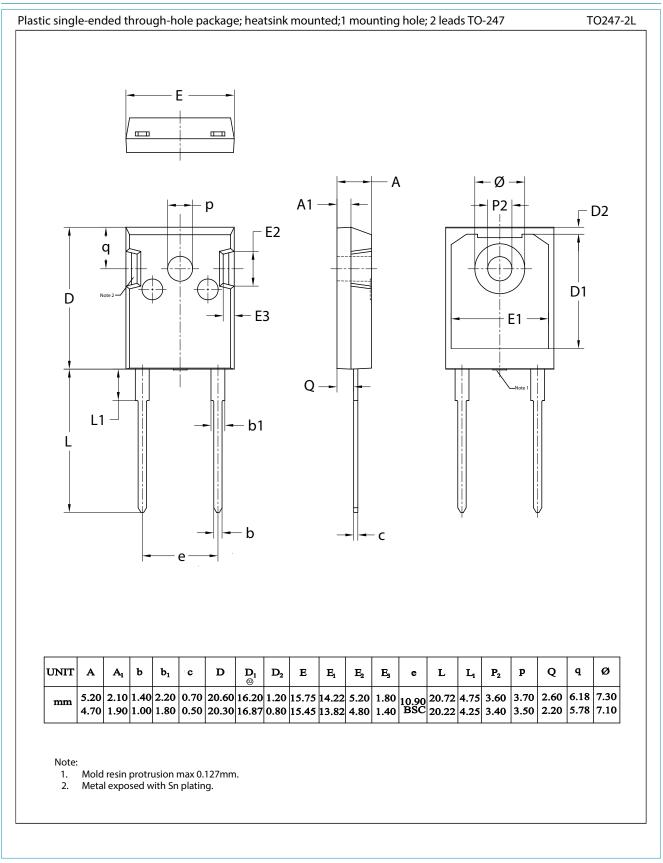




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11. Package outline



WNSC2D201200W

Silicon Carbide Diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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